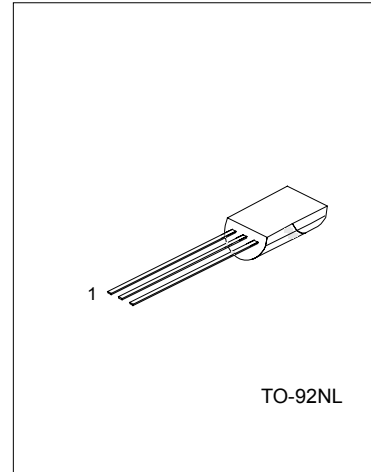


LOW FREQUENCY POWER AMPLIFIER

FEATURES

- *Low frequency power amplifier
- *Complement to 2SB562



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CB0}	25	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _c	1	A
Collector Peak Current	I _{c(peak)}	1.5	A
Collector Power Dissipation	P _C	0.9	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to base breakdown voltage	V _{(BR)CBO}	I _c =10μA, I _E =0	25			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _c =1mA, R _{BE} =∞	20			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _c =0	5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =20V, I _E =0			1	μA
DC Current transfer ratio	h _{FE}	V _{CE} =2V, I _c =0.5A (note)	85		240	
Collector to emitter saturation voltage	V _{CE(sat)}	I _c =0.8A, I _B =0.08A (note)		0.2	0.5	V
Base to emitter voltage	V _{BE}	V _{CE} =2V, I _c =0.5A (note)		0.79	1	V
Gain bandwidth product	f _T	V _{CE} =2V, I _c =0.5A (note)		190		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		22		pF

Note: Pulse test

CLASSIFICATION OF hFE

RANK	B	C
RANGE	85 - 170	120 - 240

TYPICAL PERFORMANCE CHARACTERISTICS

